



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

WBFBP-02C Plastic-Encapsulate Diodes

DS521-30LED02 Schottky barrier Diodes

DESCRIPTION

Silicon epitaxial planar

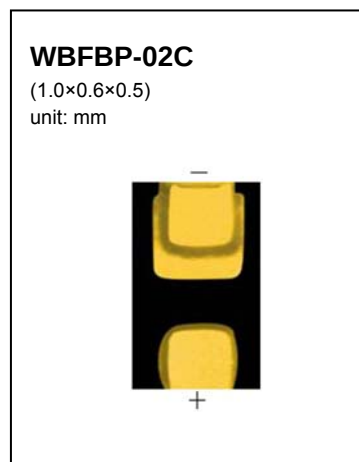
FEATURES

- Small surface mounting type
- High reliability

APPLICATION

High speed switching For Detection

For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note book PC, etc.)



MARKING: F



Maximum Ratings and Electrical Characteristics, Single Diode @T_A=25°C

Parameter	Symbol	Limits	Unit
DC reverse voltage	V _R	30	V
Mean rectifying current	I _O	100	mA
Peak forward surge current	I _{FSM}	1	A
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-40~+125	°C

Electrical Ratings @T_A=25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _F			0.35	V	I _F =10mA
Reverse current	I _R			10	μA	V _R =10V

Typical Characteristics

●Electrical characteristic curves ($T_a=25^\circ\text{C}$)

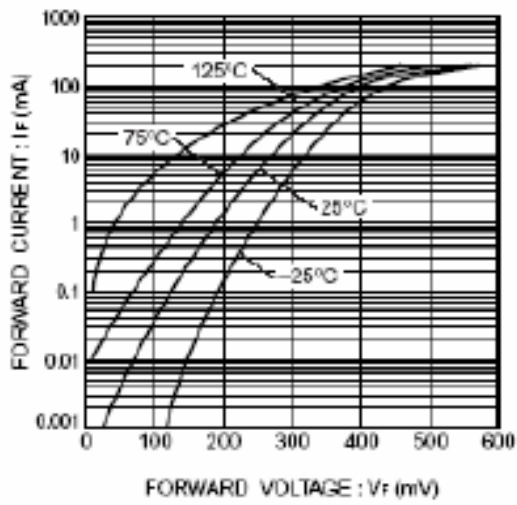


Fig.1 Forward characteristics

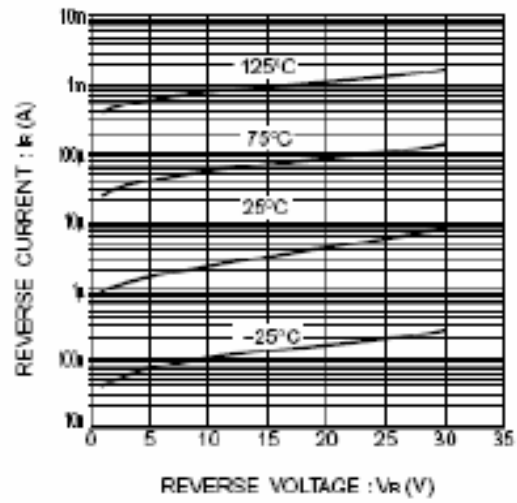


Fig.2 Reverse characteristics

